

In the Specification

Page 1, line 1, kindly change the TITLE to appear as set forth below. A Separate Markup Sheet showing the changes is attached hereto.

DUAL GATE OXIDE HIGH-VOLTAGE SEMICONDUCTOR DEVICE

Page 16, line 1, kindly change the header to appear as set forth below. The changes are shown on the Separate Markup Sheet.

DUAL GATE OXIDE HIGH-VOLTAGE SEMICONDUCTOR DEVICE

In the Claims

Kindly amend claim 12 to appear as set forth below. The changes are shown on the Separate Markup Sheet.

12. (Amended) The device of claim 8, wherein a thickness of approximately 1200A of the second gate oxide results in an increase from approximately $1e^{12} \text{ cm}^{-2}$ to approximately $2e^{12} \text{ cm}^{-2}$ of a maximum allowable charge and a decrease of approximately 30% of a specific-on-resistance, of the device.
